

Abstracts

The Gap Diode: A New High Frequency Mixer and Detector

S.J.J. Teng, P. Chen, F.J. Rosenbaum and R.E. Goldwasser. "The Gap Diode: A New High Frequency Mixer and Detector." 1982 MTT-S International Microwave Symposium Digest 82.1 (1982 [MWSYM]): 24-26.

A new metal-semiconductor device is reported whose I-V characteristic is controlled by a geometric gap between adjacent Schottky barrier regions. An improved performance low turn-on voltage GaAs diode is demonstrated at 10 through 70 GHz.

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